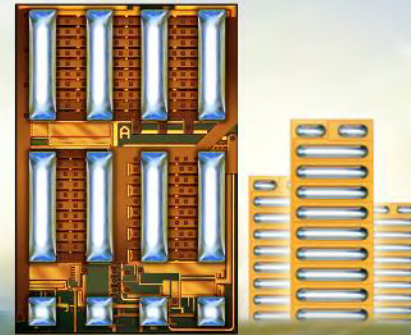


*The eGaN[®] Technology
Journey Continues*

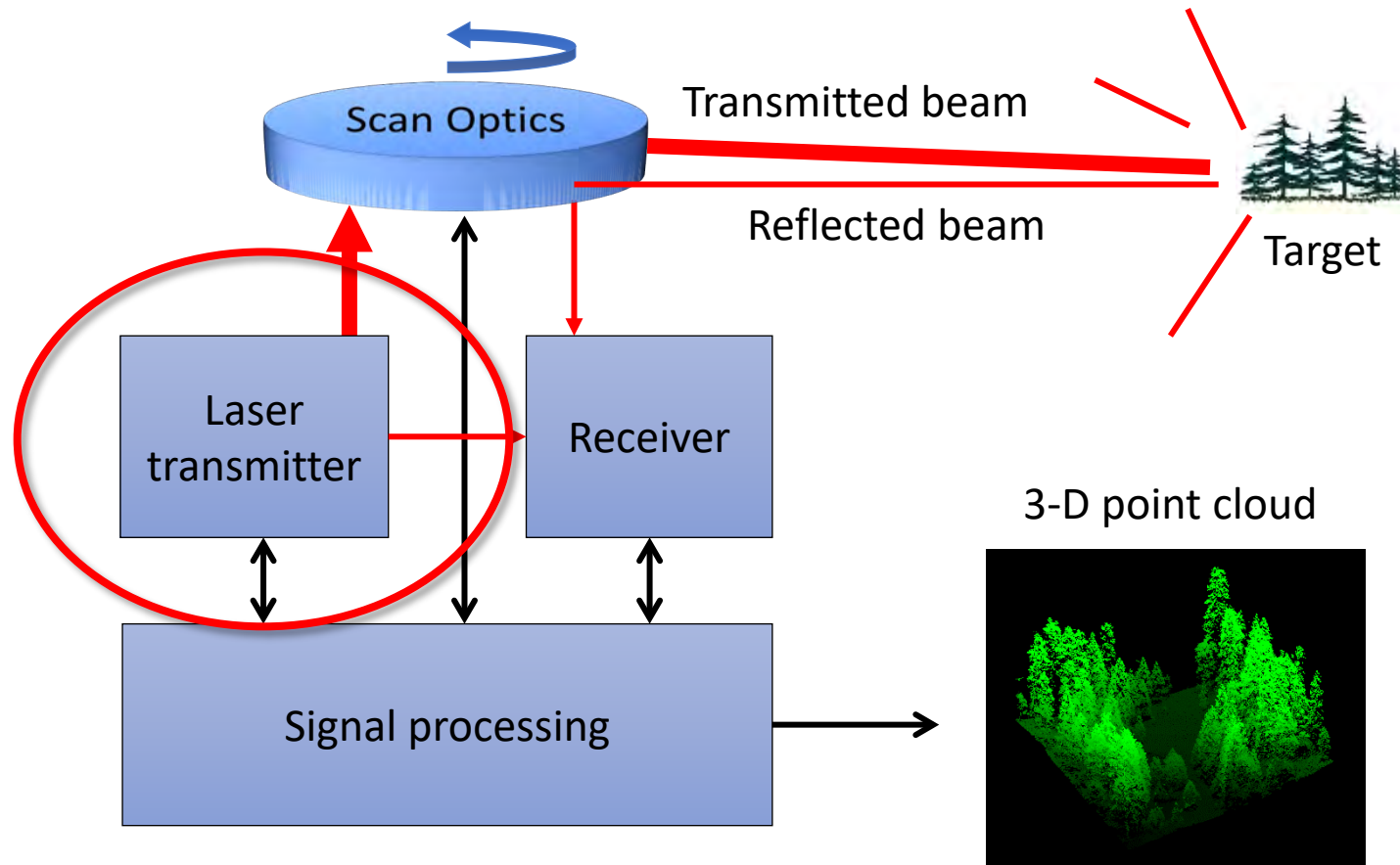


**GaN-based Solutions for Cost Effective Direct
and Indirect Time-of-Flight Lidar Transmitters**
Alex Lidow, EPC

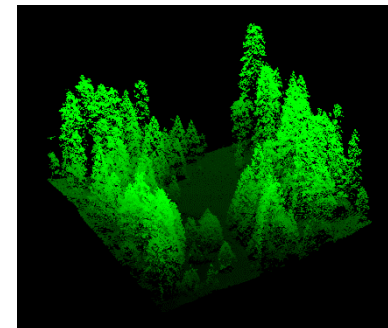
Overview

- Introduction to lidar and laser diode drivers
- Why GaN?
- Do picoHenries matter?
- State-of-the-art
- The future

What is Lidar?



3-D point cloud



http://ucanr.edu/blogs/green//blogfiles/11605_original.png

Types of lidar

- **Time of flight (ToF) for distance measurement**
- **Doppler**
- **Spectroscopic**
- **Multispectral**
- **Polarized**
- **...**

Where is ToF Lidar Used Today?



SR

Automated Guided Material Handling Robot



SR

Lidar Robotic Vacuum



LR
SR

Lidar Robotic Delivery Vehicles



LR
SR

Lidar Robotic Security Robot



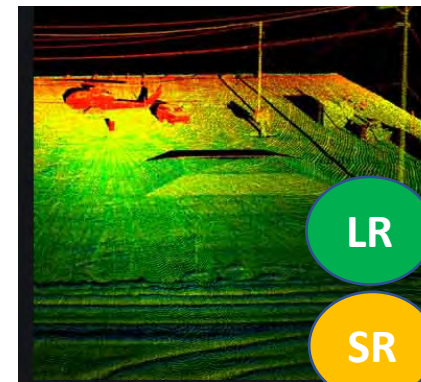
LR
SR

Drone Navigation and 3-D Mapping



SR

Humanoid Robots and Cobots



LR
SR

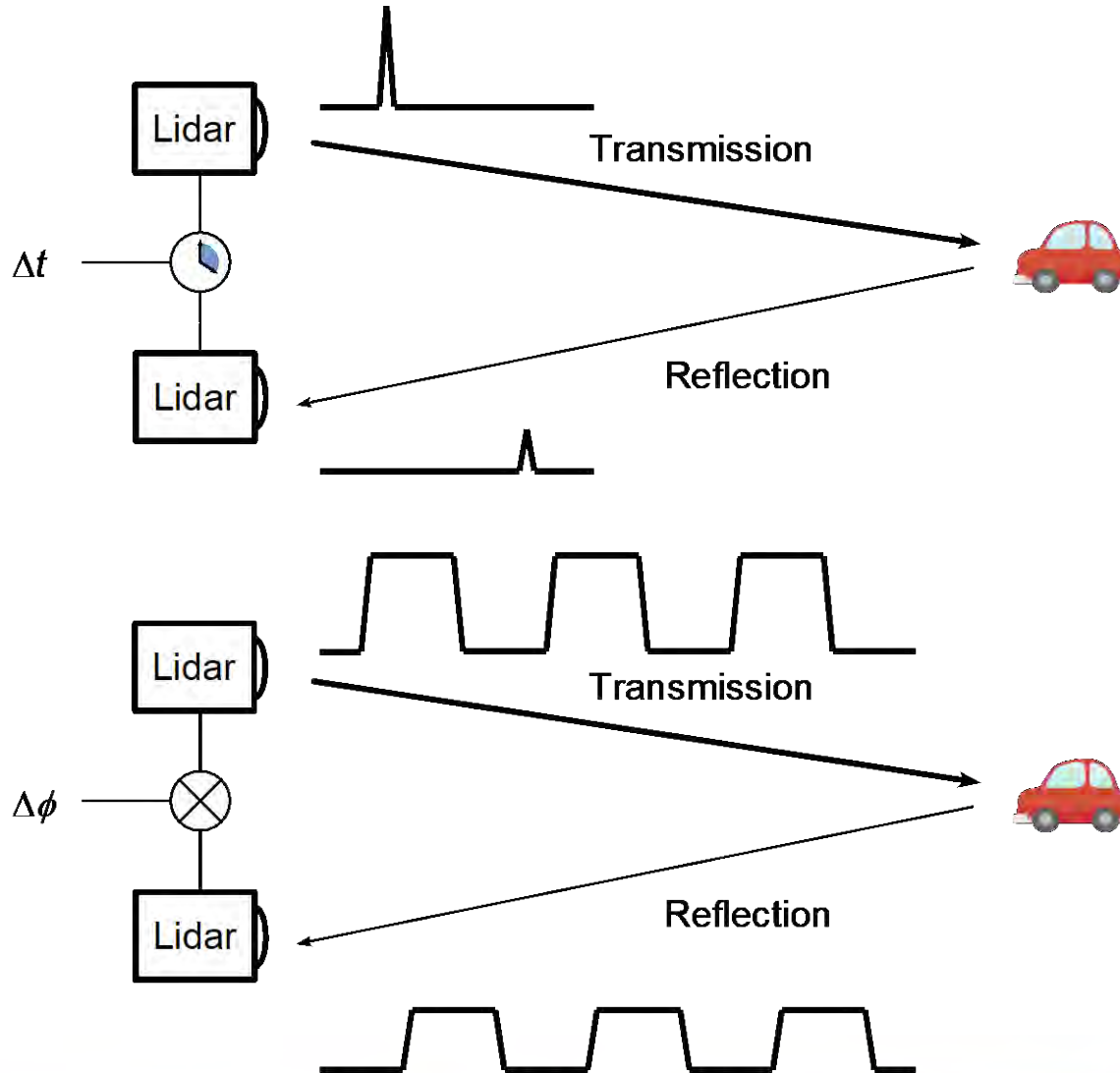
Lidar Surveillance Systems



LR
SR

Autonomous Vehicle Navigation

Direct versus Indirect (DToF vs. IToF)



Direct (DToF)

Measure time difference between TX and RX pulse

- Long range
- single point/laser
- fancy optics

Indirect (IToF)

Measure phase difference between TX and RX envelope

- “Flash” lidar
- Imaging chip detector



Importance of pulse shape (DToF)

$$d = \frac{c t_d}{2}$$

t_{d1} t_{d2}

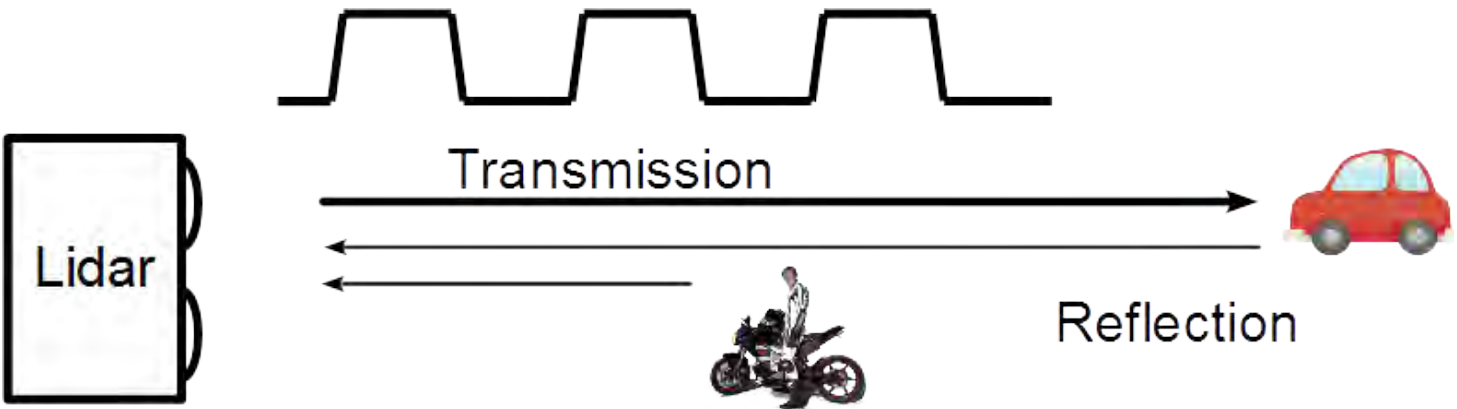
$$\frac{c \times 1 \text{ ns}}{2} = 15 \text{ cm}$$

??

Shorter pulse = better resolution



Importance of pulse shape (IToF)



Fast transition

- Linear phase and time response
- Low-cost CMOS detector
- Direct TOF readout



Slow transition

- Nonlinear response
- Extra computation required

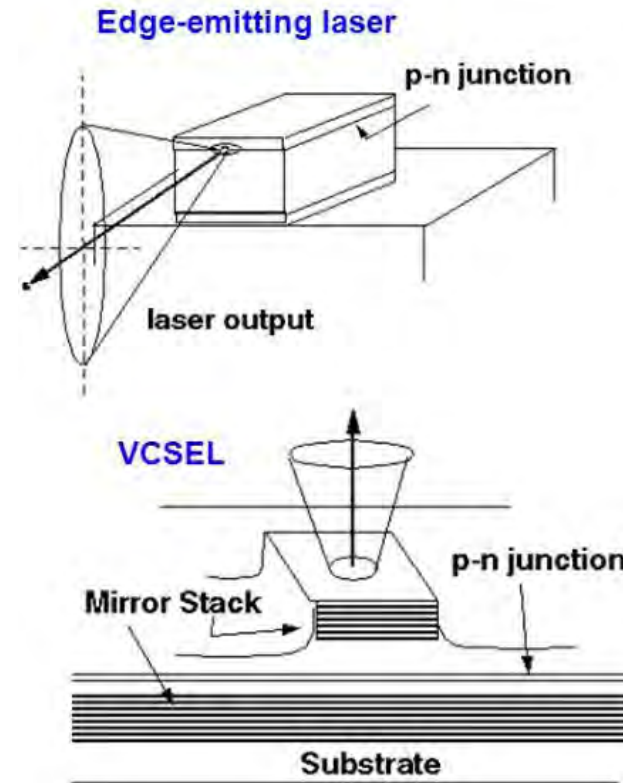
Amplitude (DToF and IToF)

- Higher pulse amplitude = increased range
- Pulse energy limits:
 - Laser thermal limitations
 - Eye safety limits
- Narrower pulse affords higher amplitude

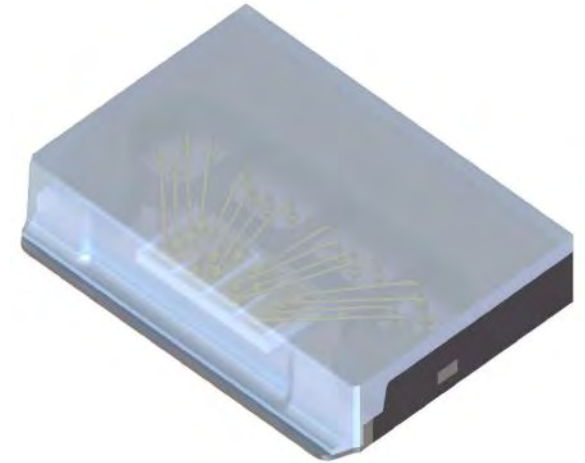


Laser Diodes

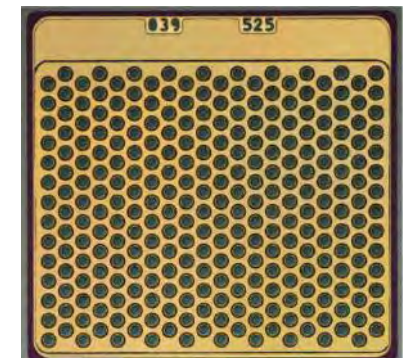
- Laser diodes are most common light source
 - Fast response, 100 ps or less
 - Peak optical power from $< 1\text{ W}$ to $> 1\text{ kW}$
 - Cost effective
 - Available in useful wavelengths (850 nm, 905 nm, 940 nm, 1550 nm)



Introduction to nanophotonics Alexey Belyanin Department of Physics, Texas A&M University



https://www.osram.com/ecat/SMT%20Laser%20SPL%20S4L90A_3%20A01/com/en/class_pim_w eb_catalog_103489/prd_pim_device_4071163/



<https://ii-vi.com/product/high-power-vcSEL-array/>

DToF Pulse Width and Amplitude

Target: Up to 200 m to 300 m

Pulse: 5 ns to 50ns

Higher power: 50 A to 500 A



Target: Up to 10 m

Pulse: 0.5 ns to 5ns

Lower power: 5 A to 50 A

IToF Pulse Width and Amplitude



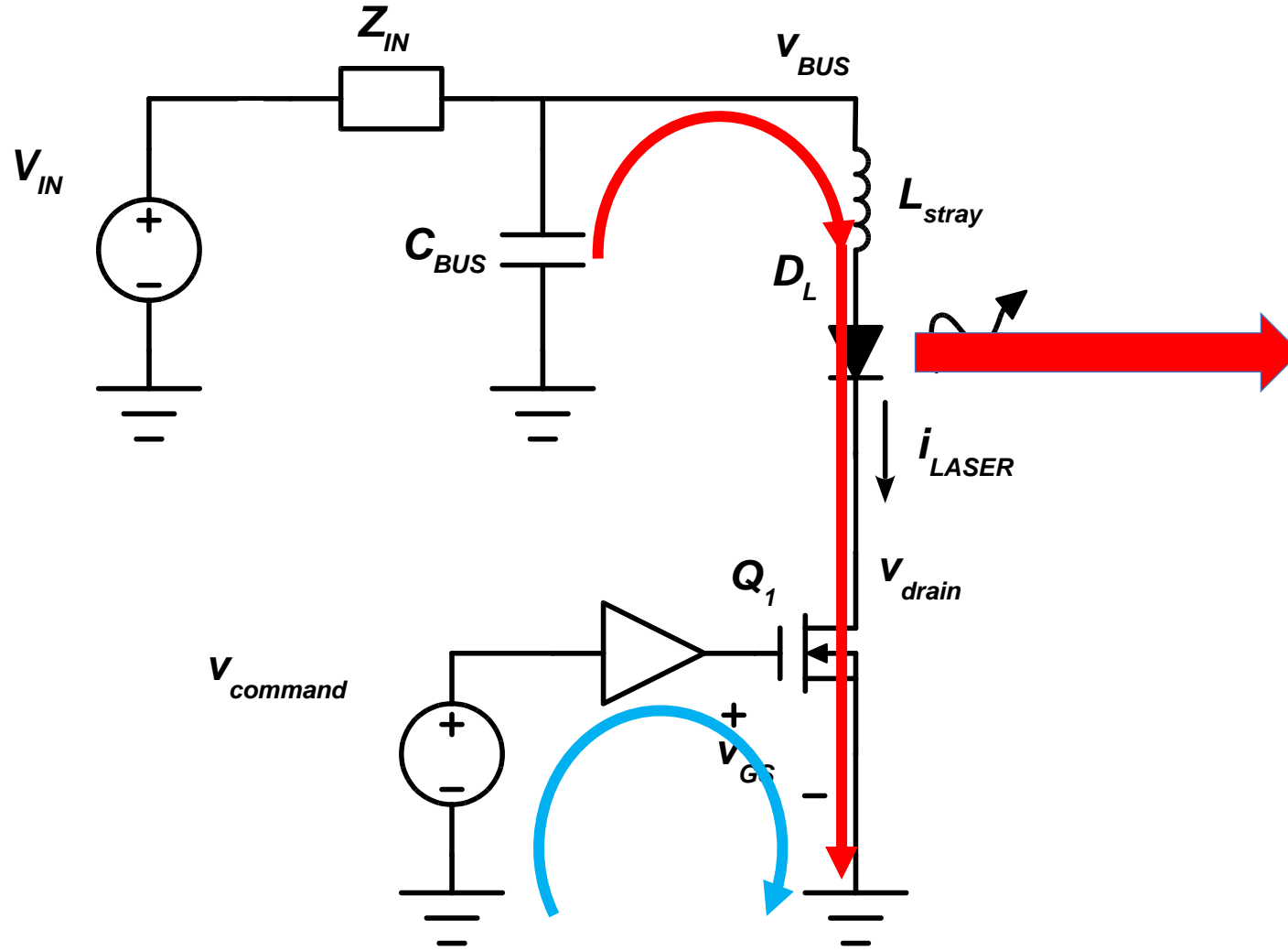
Target: 10 m to ??? (50+ m)
Higher power
10 A to ??? (hundreds)
Tens of MHz



Target: Up to 10 m
Lower power
1 A to 10 A
50 MHz to 200 MHz



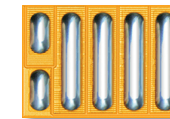
Laser Driver Circuit



Why GaN?

Parameter	EPC2212	Best in class
Technology	eGaN FET	Si MOSFET
$V_{DS,max}$ [V]	100	100
$R_{DS(on)}$ [mΩ]	14	21
$I_{pulse,max}$ [A] (@ 4.5 V)	75	80
Q_{Gtot} [nC]	3.2	7.6
R_{gate} [Ω]	0.4	1.0
$R_{gate} \cdot Q_{Gtot}$ [Ω·nC]	1.3	7.6
L_{gate} [nH]	< 0.1	3.0
L_{source} [nH]	< 0.05	0.3
L_{drain} [nH]	< 0.05	1.0
Package [mm x mm]	LGA 2.1 x 1.6	DFN 3.3x3.3
AEC Q101	YES	NO

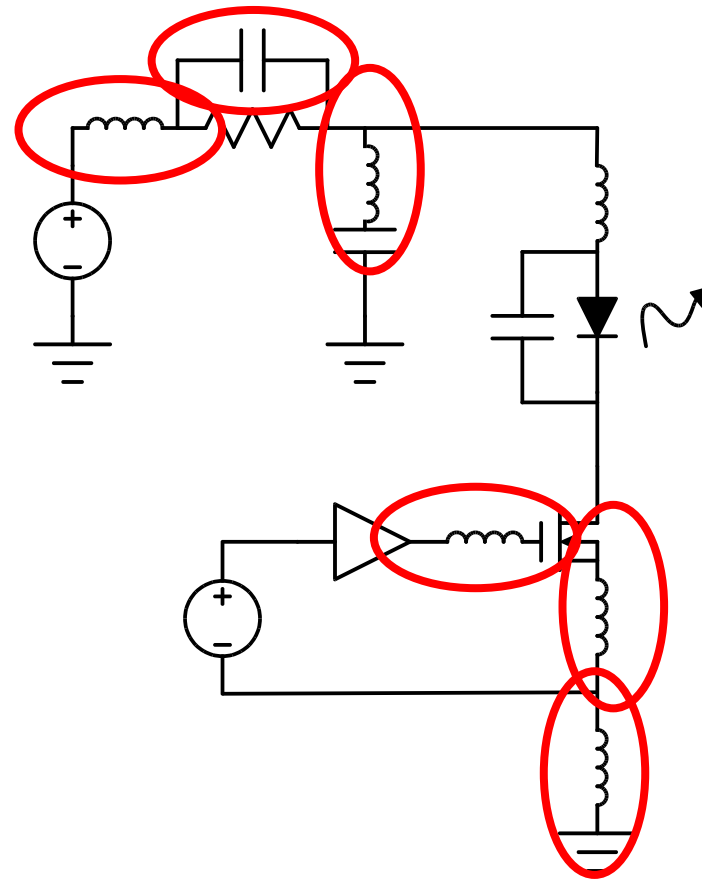
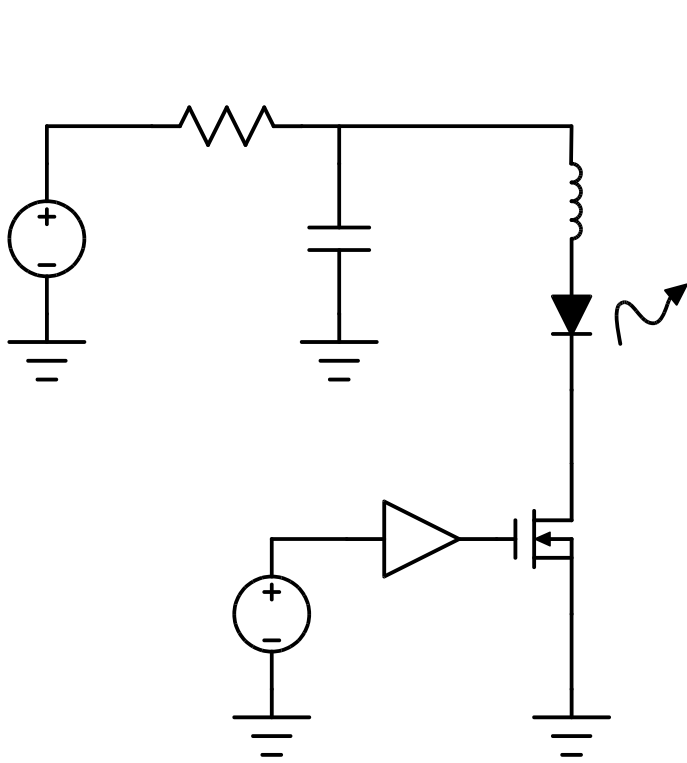
eGaN FET



Si MOSFET



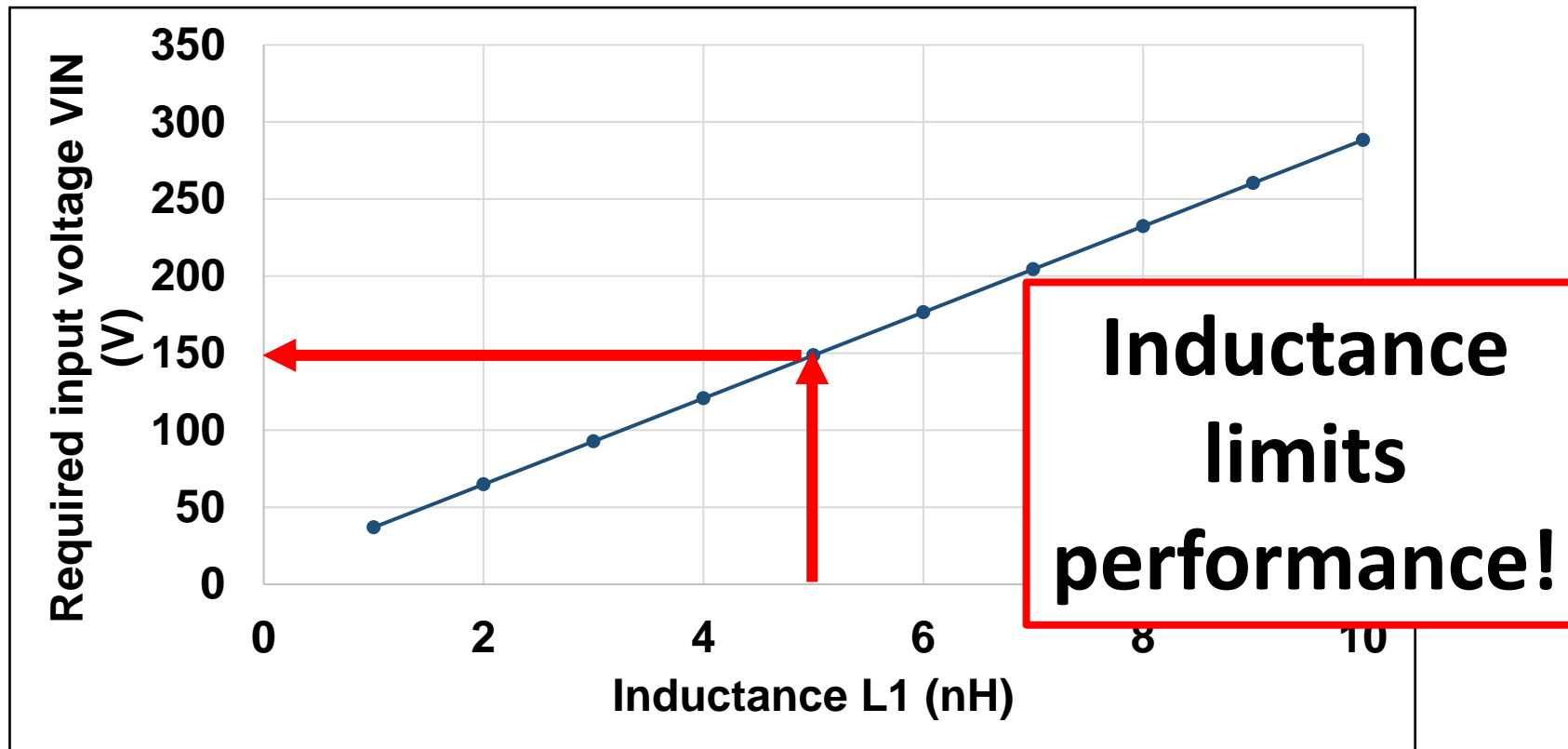
Simple?



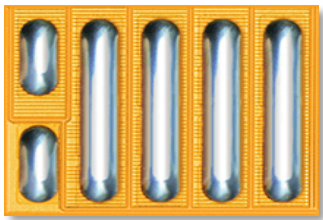
Not so simple...

Impact of Power Loop Inductance

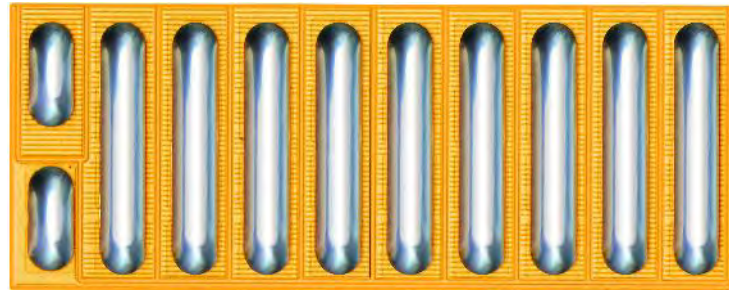
Design conditions: Peak current $I_{DL,pk} = 40 \text{ A}$, $t_w = 3 \text{ ns}$



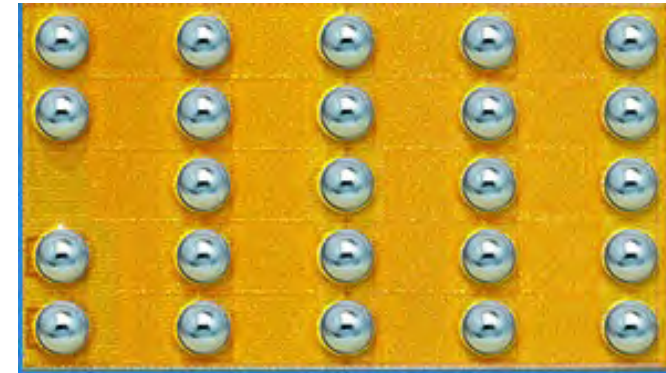
Low Inductance Starts With FETs



EPC2212
100 V
75 A pulse

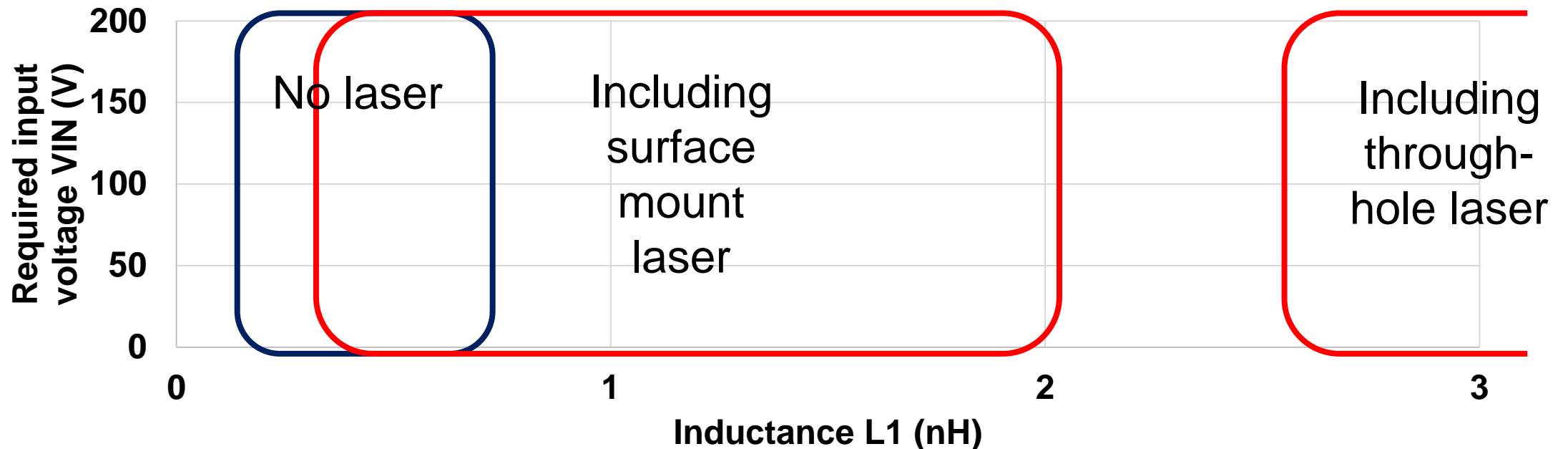


EPC2001C
100 V
150 A pulse



EPC2034C
200 V
213 A pulse

Practical Power Loop Inductance

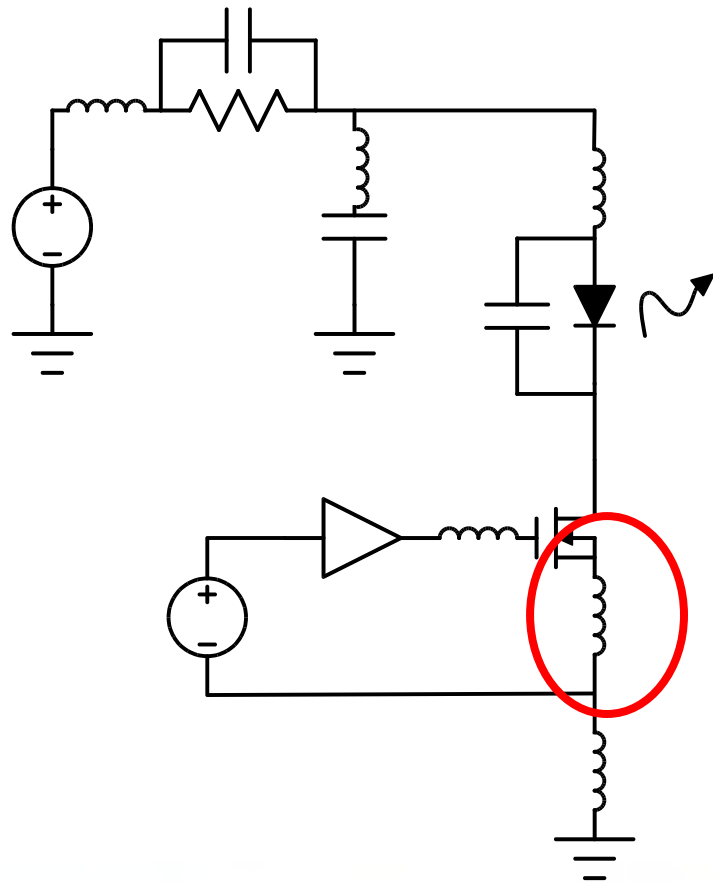


Power loop includes:

- Main Power FET (chip scale package)
- Capacitor bank
- Mounting area for laser diode
- Current measurement shunt (in some cases)

Question: Does 50 pH Matter?

Answer: Yes, if it's common source inductance (CSI)



Typical di/dt :

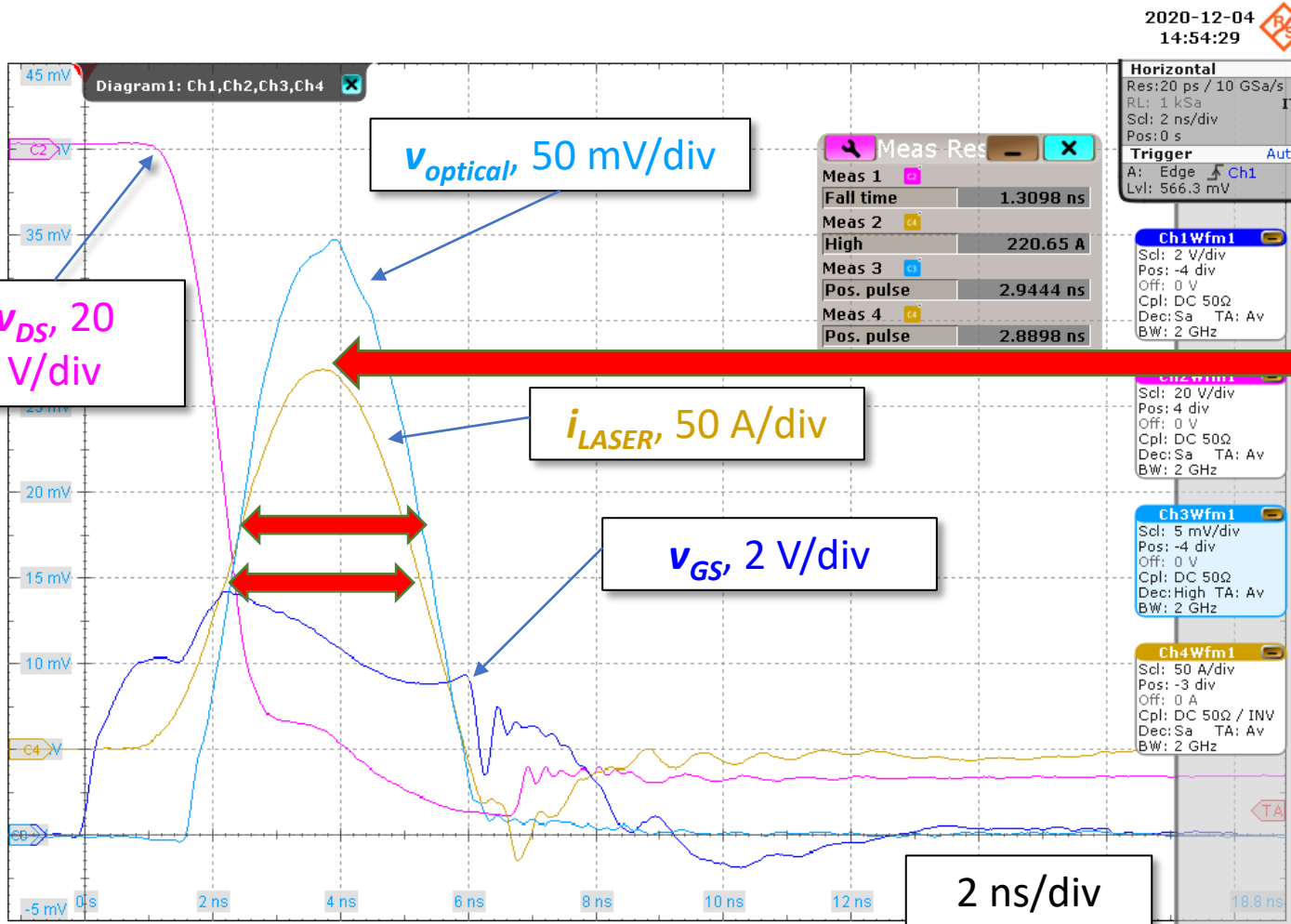
$$\frac{di_S}{dt} = \frac{di_D}{dt} = \frac{100 \text{ A}}{\text{ns}}$$

$$L_{CSI} = 50 \text{ pH}$$

$$v_{CSI} = L_{CSI} \frac{di_S}{dt} = 5 \text{ V}$$

50 pH matters a lot!!

EPC2034C 200 V eGaN FET



FET EPC2034C
4x1 laser B
 $V_{bus} = 150 V$

$I_{LASER,peak} = 221 A$

Current $t_{pw} = 2.89 ns$

Optical $t_{pw} = 2.94 ns$

What's New?

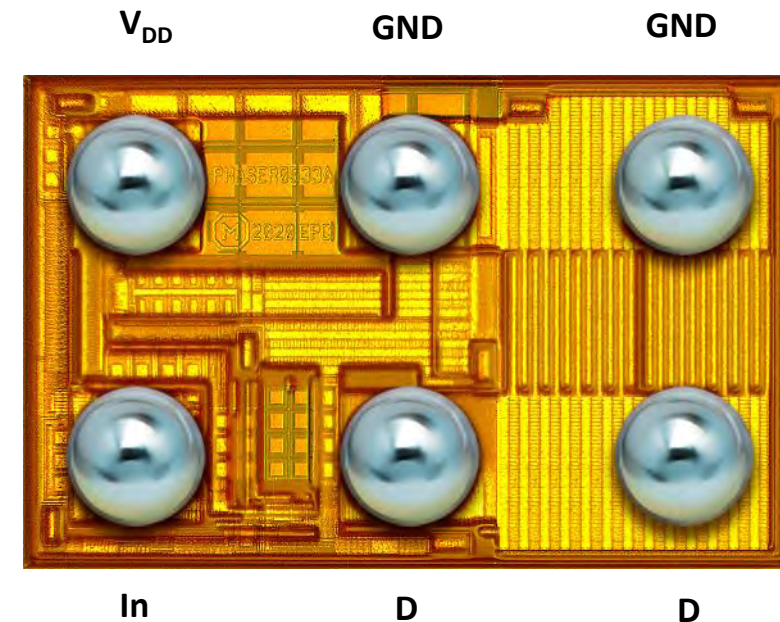
Even 10-20 pH CSI has noticeable effect on performance

Integration

- Reduce CSI to a few pH
- Replace several parts with a single part
- Enhanced reliability
- Reduced driver area
- Reduced cost

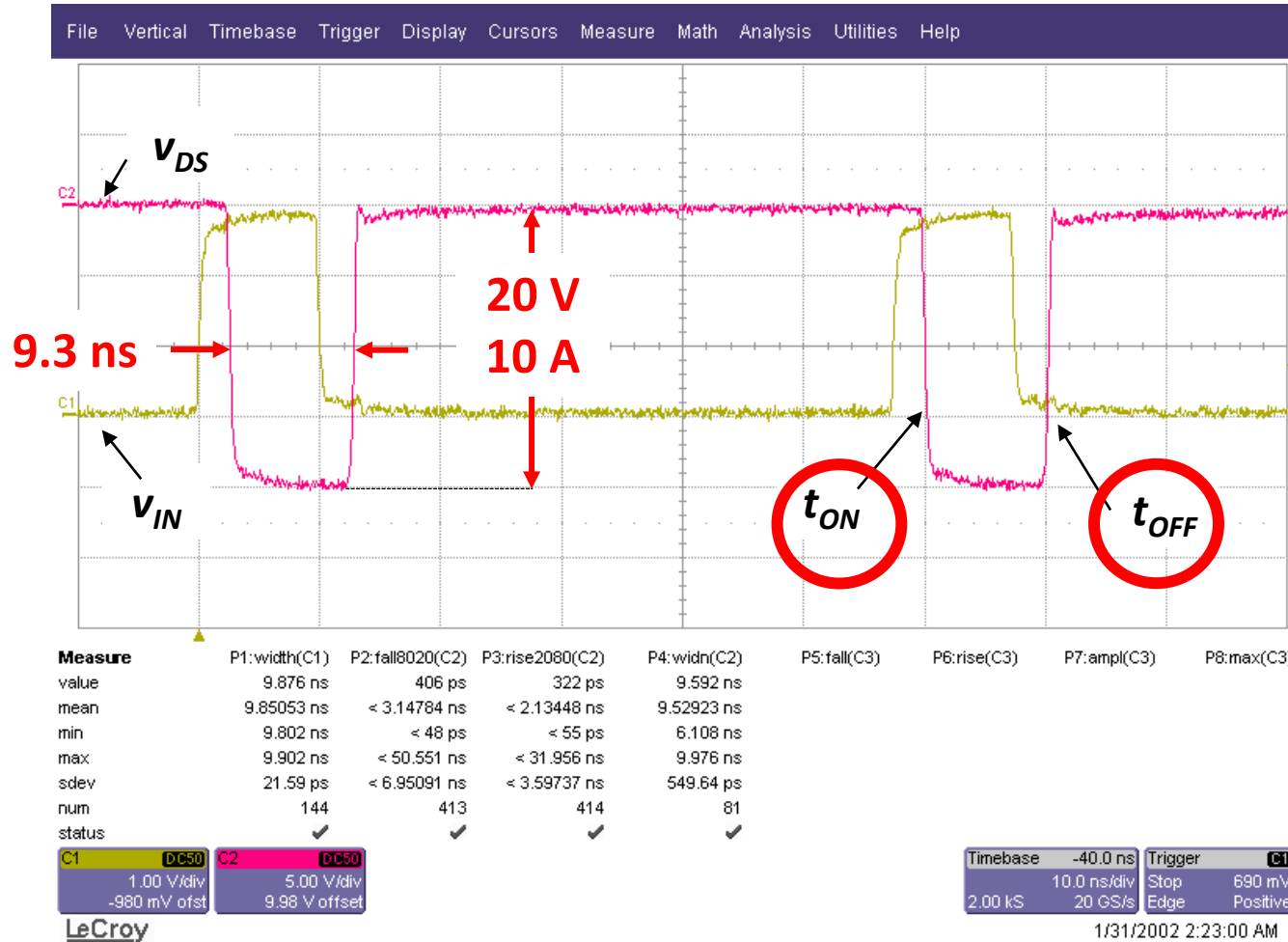
EPC21601 Laser Driver IC

- 40 V, 10 A FET with integrated gate driver
- 3.3V logic level input



1.0 mm x 1.5 mm

EPC21601



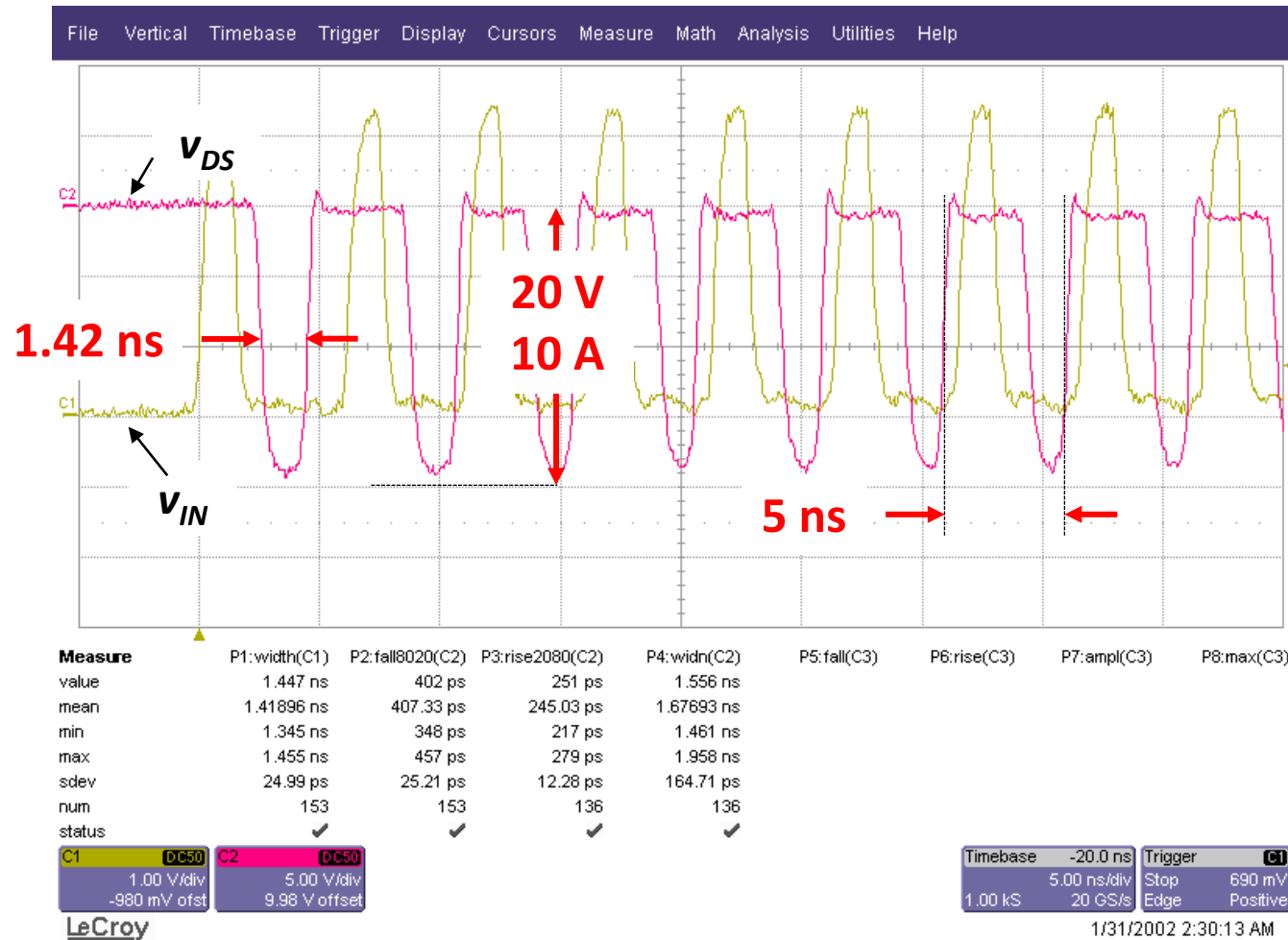
IC EPC21601
2 Ω resistive load
 $V_{bus} = 20$ V

$$I_{LOAD,peak} = 10$$
 A

$$V_{DS} t_{ON} = 410$$
 ps

$$V_{DS} t_{OFF} = 320$$
 ps

EPC21601



IC EPC21601
2 Ω resistive load
 $V_{bus} = 20\text{ V}$

$I_{LOAD,peak} = 9.3\text{ A}$

$V_{DS} t_{ON} = 407\text{ ps}$

$V_{DS} t_{OFF} = 245\text{ ps}$

200 MHz

ToF Laser Drivers



New IToF Driver

EPC9150

200 V, > 200 A

EPC9126 and EPC9126HC

100 V, 70A and 135A (HC version)

EPC9154

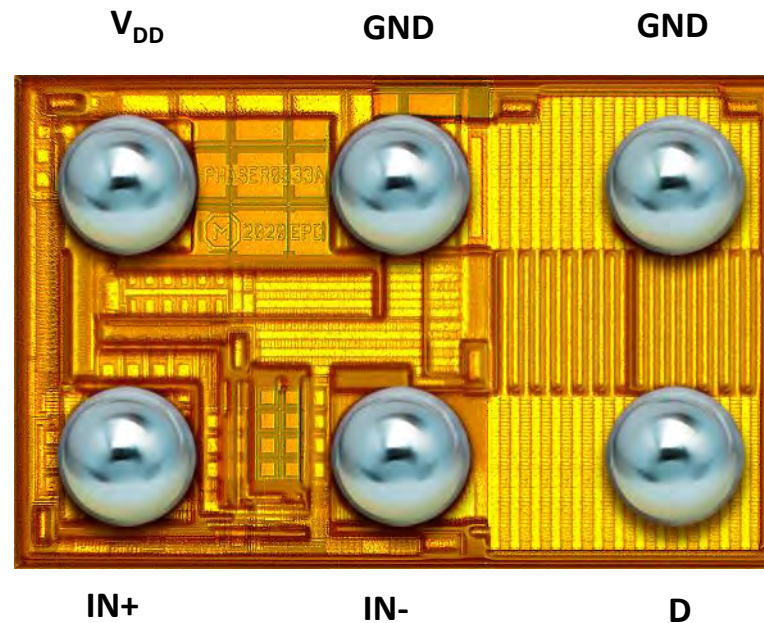
40 V, 10 A, 200 MHz

Schematics, Gerbers, and App notes available at EPC's website

What's Next?

EPC21603 Laser Driver IC

- 40 V, 10 A FET with integrated gate driver
- **LVDS (low voltage differential signal) input**

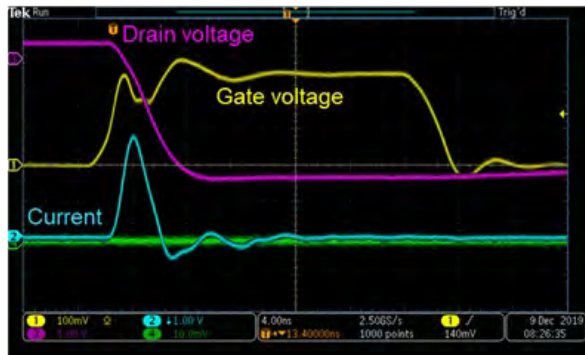


1.0 mm x 1.5 mm

**March 16
Launch**

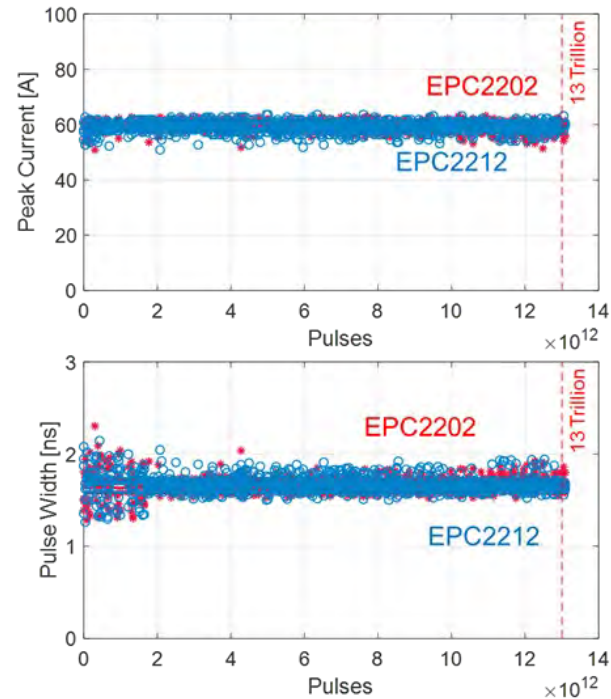
Reliability

Test waveforms

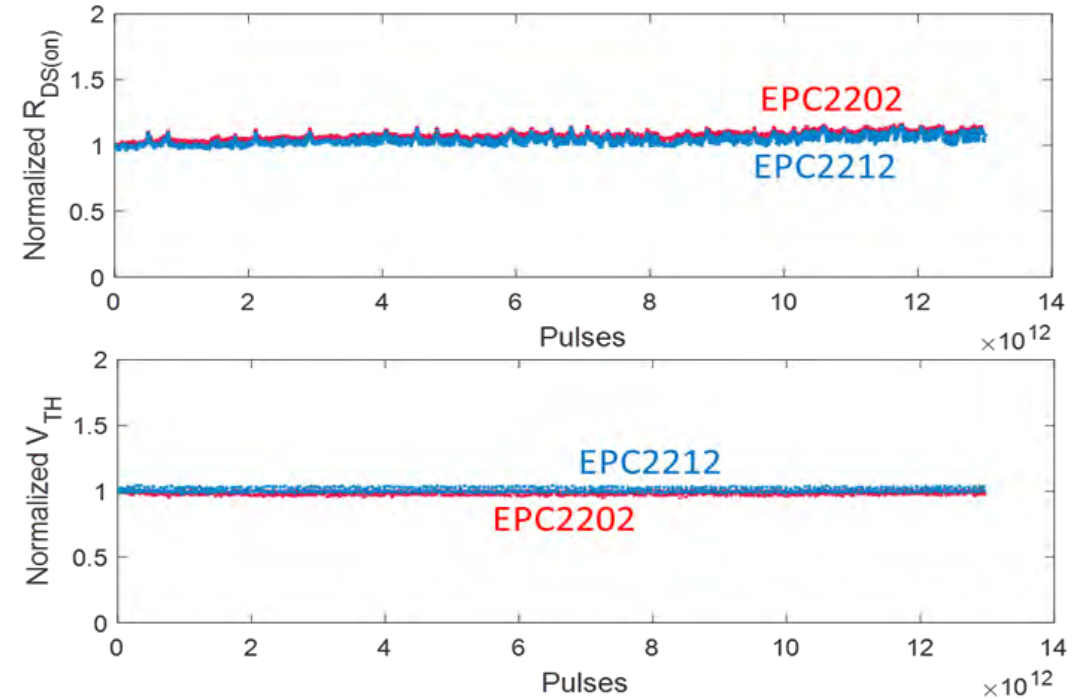


- AEC-Q101 series of discrete FETs
 - 8 samples (>7000h)
 - 0 failures and perfect pulse stability

Pulse performance



FET parameter stability



Stable after 13 Trillion Cycles

Conclusion

- Time-of-flight lidar drivers are a pulsed power application
- Pulse requirements differ with lidar range and purpose.
- When using GaN FETs, inductance dominates the design
- eGaN FETs are best choice for high performance laser drivers